



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
-30V	12mΩ @ V _{GS} = -10V	-35A		
	21mΩ @ V _{GS} = -4.5V	-25A		

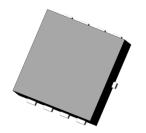
Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- DC-DC Converters





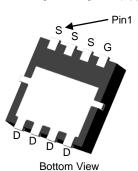
Top View

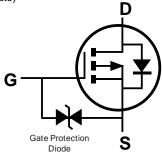
Features and Benefits

- 100% Unclamped Inductive Switching (Test in Production) -Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: PowerDI®3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)





Equivalent Circuit

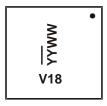
Ordering Information (Note 5)

	Part Number	Case	Packaging			
	DMP3018SFVQ-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel			
DMP3018SFVQ-13 PowerDl3333-8 (Type UX) 3,000/Tape & Reel			3,000/Tape & Reel			
Notes:	Notes: 1, No purposely added lead, Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



V18 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±25	V		
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-11 -9	А
Continuous Drain Current (Note 8) V _{GS} = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-35 -25	А
Maximum Continuous Body Diode Forward Curren	Is	-30	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	I _{DM}	-70	Α		
Pulsed Body Diode Forward Current (10µs Pulse,	I _{SM}	-70	Α		
Avalanche Current (Note 9) L = 1mH	I _{AS}	-14	Α		
Avalanche Energy (Note 9) L = 1mH	E _{AS}	104	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	133	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	1.9	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	66	°C/W
Total Power Dissipation (Note 8)		P _D	30	W
Thermal Resistance, Junction to Case (Note 8)		Rejc	3.7	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	_	12	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	_	21	11122	$V_{GS} = -4.5V, I_D = -8.5A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{iss}	_	2147	_	pF	\\ 45\\\\\ 0\\	
Output Capacitance	Coss	_	407	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	358	_	pF	T = 1.0WHZ	
Gate Resistance	R_g	_	24	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	_	28	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	51	_	nC	V _{DS} = -15V. In = -11.5A	
Gate-Source Charge	Q_{gs}	_	6.6	_	nC	VDS = -15V, ID = -11.5A	
Gate-Drain Charge	Q_{gd}	_	15	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	7.8	_	ns		
Turn-On Rise Time	t _R	_	19.9	_	ns	$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	57.5	_	ns	$R_G = 6\Omega$, $I_D = -11.5A$	
Turn-Off Fall Time	t _F	_	42.8	_	ns	1	
Reverse Recovery Time	t _{RR}	_	21.5	_	ns	1 11 EA dl/dt 100 A /··-	
Reverse Recovery Charge	Q _{RR}	_	11.6	_	$I_{S} = -11.5A$, $dI/dt = 100A/\mu s$		

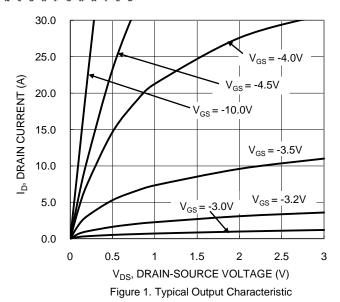
Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.
- 10. Short duration pulse test used to minimize self-heating effect.

 11. Guaranteed by design. Not subject to product testing.







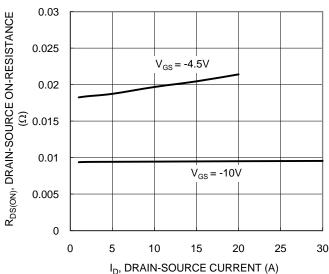


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

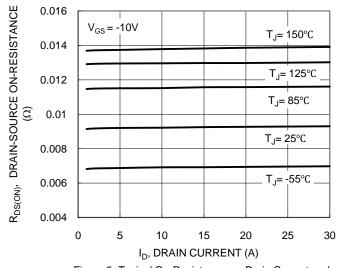
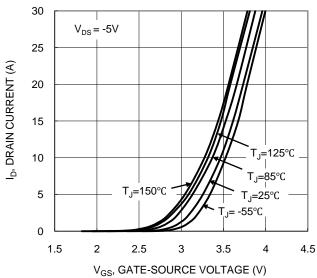


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V)
Figure 2.Typical Transfer Characteristic

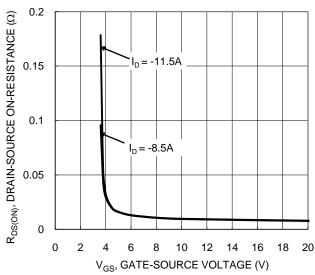


Figure 4. Typical Transfer Characteristic

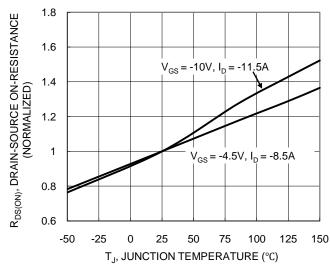


Figure 6. On-Resistance Variation with Junction Temperature





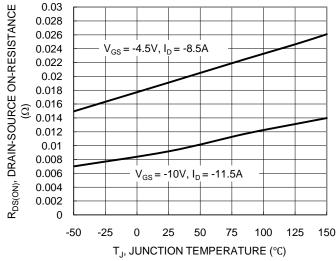
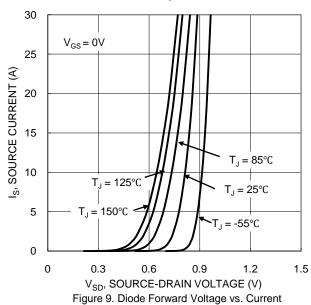
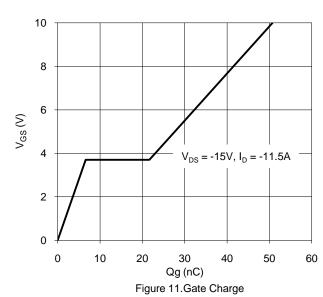


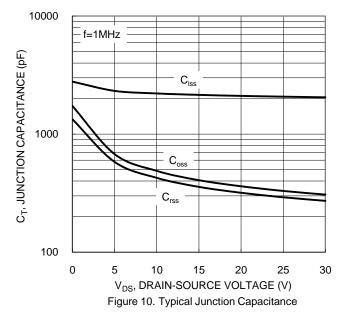
Figure 7. On-Resistance Variation with Junction Temperature





3 $V_{\text{GS(TH)}}$, GATE THRESHOLD VOLTAGE (V) 2.8 2.6 $I_D = -1mA$ 2.4 2.2 $I_{D} = -250 \mu A$ 2 1.8 1.6 1.4 1.2 1 -50 -25 0 25 50 75 100 125 150 T_{.I}, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature



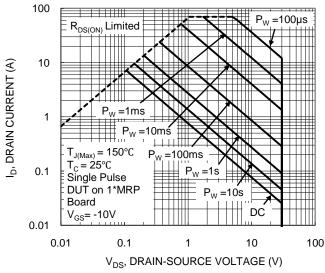


Figure 12. SOA, Safe Operation Area



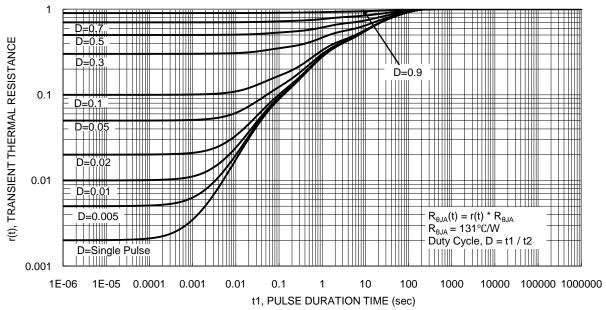


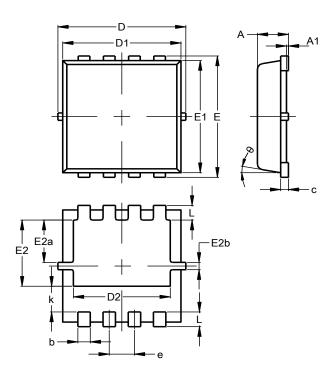
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

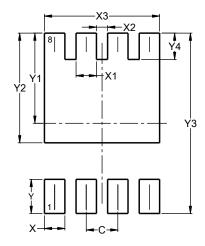


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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